## ABSTRACT OF THE DISCLOSURE

光信:セイコーインスツルメンツ(休)刈り財産部

In a metal-oxide semiconductor transistor in which a gate width per unit area can be increased through a method other than microfabrication, there is provided a high driving performance metal-oxide semiconductor transistor in which a single or a plurality of semiconductor devices and another circuit can be consolidated on one chip. The metal-oxide semiconductor transistor includes a plurality of linear concave portions that are arranged in a channel width direction.